

IN THE CLAIMS

Please cancel Claims 5, 9, 14, 15, and 17 without prejudice or disclaimer.

Claims 1-5 (cancelled)

Claim 6 (currently amended): The method for manufacture of an insulation film according to claim 5 11 wherein the pitch L and the pitch p satisfy the following equation: $m p = n L$ wherein n and m are integers that satisfy the equation $n < m$.

Claim 7 (previously presented): The method for manufacture of an insulation film according to claim 6 wherein the step of forming the through holes further comprises the steps of:

forming the through holes by collective punching out at the effective sprocket hole formation width of the through holes along the transverse direction of the insulation film in a region of length $n L$ along the length-wise direction of the insulation film;

moving the insulation film a length $n L$ in the length-wise direction by means of the sprocket holes; and

repeating these two steps alternately.

Claim 8 (previously presented): The method for manufacture of an insulation film according to claim 6 wherein the method further comprises a step of forming a two-dimensional array of circuit patterns upon the insulation film according to size of the semiconductor package and a conductor pattern electrically connected with the array of circuit patterns.

Claim 9 (cancelled)

Claim 10 (currently amended): The method for manufacture of a semiconductor package according to claim 9 11 wherein the method further comprises the step of plating each of the circuit patterns upon the insulation film using the conductor pattern.

Claim 11 (currently amended): A method for manufacture of a semiconductor package comprising the steps of: providing an insulation film, forming two rows of sprocket holes comprising a plurality of sprocket holes formed at a pitch L along both edges of the insulation film, forming a two-dimensional array of through holes between the rows of sprocket holes, each through hole in said array spaced from adjacent through holes by a pitch p , forming a two-dimensional plurality of circuit patterns upon the insulation film according to size of the semiconductor package, forming a conductor pattern electrically connected with the plurality of circuit patterns having a main line surrounding a perimeter of the plurality of circuit patterns and a sub-line electrically connecting each of the circuit patterns to the main line;

mounting a semiconductor chip within a respective prescribed region of each circuit pattern of the insulation film and electrically connecting the semiconductor chip with the circuit pattern;

performing resin sealing for partitioning off each region enclosed by the main line of the conductor pattern; and

cutting apart into individual semiconductor packages by dicing along the sub-lines of the insulation film,

wherein the dicing step is carried out by use of a dicing blade having a blade trim width wider than the wiring width of the sub-line of the conductor pattern whereby the sub-line is not left behind upon the insulation film.

Claim 12 (previously presented): The method for manufacture of an insulation film according to claim 7 wherein the method further comprises a step of forming a two-dimensional array of circuit patterns upon the insulation film according to size of the semiconductor package and a conductor pattern electrically connected with the plurality of circuit patterns.

Claim 13 (previously presented): A method for manufacture of a semiconductor package comprising the steps of: providing an insulation film, forming two rows of sprocket holes comprising a plurality of sprocket holes formed at a pitch L along both edges of the insulation film, forming a two-dimensional array of through holes between the rows of sprocket holes, each through hole in said array spaced from adjacent through holes by a pitch p , forming a two-dimensional plurality of circuit patterns upon the insulation film according to size of the semiconductor package, forming a conductor pattern electrically connected with the plurality of circuit patterns having a main line surrounding a perimeter of the plurality of circuit patterns and a sub-line electrically connecting each of the circuit patterns to the main line;

mounting a semiconductor chip within a respective prescribed region of each circuit pattern of the insulation film and electrically connecting the semiconductor chip with the circuit pattern;

performing resin sealing for partitioning off each region enclosed by the main line of the conductor pattern; and

cutting apart into individual semiconductor packages by dicing along the sub-lines of the insulation film,

wherein the method further comprises the step of plating each of the circuit patterns upon the insulation film using the conductor pattern, and

wherein the dicing step is carried out by use of a dicing blade having a blade trim width wider than the wiring width of the sub-line of the conductor pattern whereby the sub-line is not left behind upon the insulation film.

Claims 14 (cancelled)

Claim 15 (currently amended): The method of Claim 14 Dan what claim?, wherein said step of providing an insulation film comprises:

providing an insulation film having rows of sprocket holes at a pitch L along the edges of said film, and a two-dimensional array of through holes in said film between the rows of sprocket holes, said through holes arranged relative to one another in said

array at a pitch p and continuously along and transversely across said film within circuit pattern regions on said film.

Claim 16 (previously presented): A method of packaging a semiconductor device, comprising the steps of:

- providing an insulation film having rows of sprocket holes at a pitch L along the edges of said film and a two-dimensional array of through holes in said film between the rows of sprocket holes, said through holes arranged relative to one another in said array at a pitch p ;

- mounting a semiconductor chip over a number of said through holes;

- sealing said semiconductor chip and a portion of said insulation film in resin; and

- cutting said insulation film surrounding said semiconductor chip to release said resin-sealed chip from the remainder of said insulation film,

- wherein said step of providing an insulation film comprises:

- providing an insulation film having rows of sprocket holes at a pitch L along the edges of said film, and a two-dimensional array of through holes in said film between the rows of sprocket holes, said through holes arranged relative to one another in said array at a pitch p and continuously along and transversely across said film within circuit pattern regions on said film, and

- wherein said circuit pattern regions are separated by sub-lines of a conductor pattern, and wherein said step of cutting said insulation film comprises cutting said film with a blade having a blade trim width wider than said sub-line is not left behind upon the insulation film after said cutting step.

Claim 17 (cancelled)

Claim 18 (currently amended): The method of Claim 44 16, further comprising the step of depositing solder in selected ones of said number of through holes.

Claim 19 (currently amended): The method of Claim 44 16, further comprising the step of depositing metal in selected ones of said number of through holes.